

# Schottky barrier diode

## RB481K

### ●Applications

Low current rectification

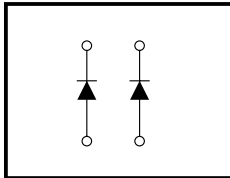
### ●Features

- 1) Small surface mounting dual element parallel type. (UMD4)
- 2) Extremely low forward voltage.
- 3) This is a composite component and is ideal for reducing the number of components used.
- 4) High reliability.

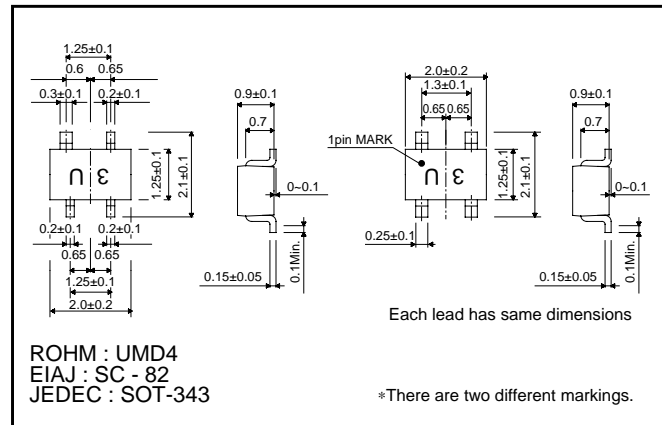
### ●Construction

Silicon epitaxial planar

### ●Circuit



### ●External dimensions (Units: mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	30	V
DC reverse voltage	$V_R$	30	V
Mean rectifying current	$I_o$	0.2	A
Peak forward surge current*	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40~+125	°C

\* 60 Hz for 1

Diodes

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>F1</sub>	–	–	0.28	V	I <sub>F</sub> =1mA
	V <sub>F2</sub>	–	–	0.33	V	I <sub>F</sub> =10mA
	V <sub>F3</sub>	–	–	0.43	V	I <sub>F</sub> =100mA
	V <sub>F4</sub>	–	–	0.50	V	I <sub>F</sub> =200mA
Reverse current	I <sub>R</sub>	–	–	30	μA	V <sub>R</sub> =10V

●Electrical characteristic curves (Ta=25°C)

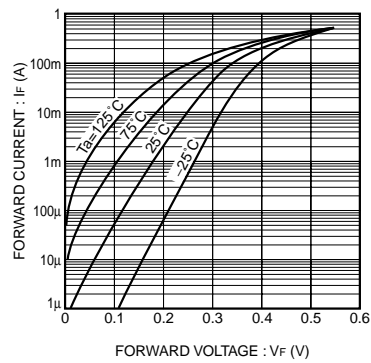


Fig. 1 Forward temperature characteristic

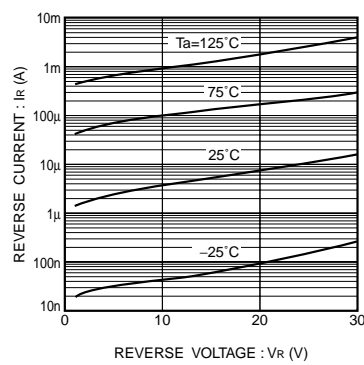


Fig. 2 Reverse temperature characteristic

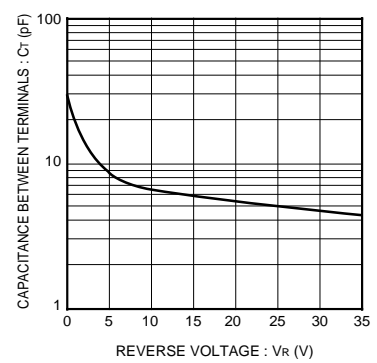


Fig. 3 Capacitance between terminals characteristic